



P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

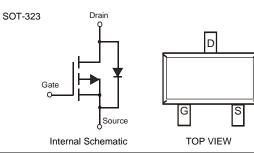
- P-Channel MOSFET
- Low On-Resistance
 - 150 m Ω @ V_{GS} = -4.5V
 - 200 m Ω @ $V_{GS} = -2.5V$
 - 240 mΩ @ V_{GS} = -1.8V
- Very Low Gate Threshold Voltage V_{GS(th)} ≤ 1V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)







Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V _{GSS}	±12	V
Drain Current (Note 1)	$T_A = 25$ °C $T_A = 70$ °C	I _D	-1.5 -1.0	Α
Pulsed Drain Current		I _{DM}	-5	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_{D}	250	mW
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB.
- No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

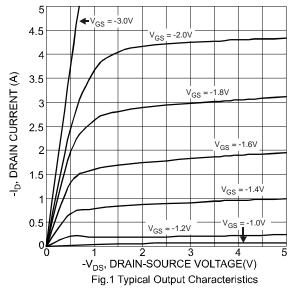


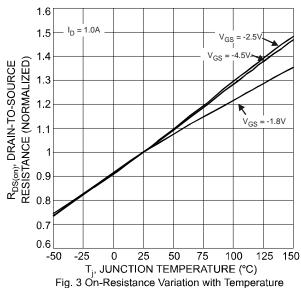
Electrical Characteristics @T_A = 25°C unless otherwise specified

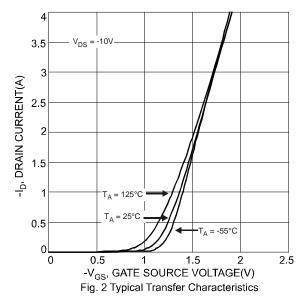
Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage		BV _{DSS}	-20		_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	$T_J = 25$ °C $T_J = 125$ °C	I _{DSS}			-1.0 -5.0	μΑ	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage		Igss		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage		$V_{GS(th)}$	-0.45	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance		R _{DS (ON)}	_	92 134 180	150 200 240	mΩ	$V_{GS} = -4.5V$, $I_D = -2.0A$ $V_{GS} = -2.5V$, $I_D = -1.5A$ $V_{GS} = -1.8V$, $I_D = -0.5A$
Forward Transconductance		g _{FS}		3.1	_	S	$V_{DS} = -10V, I_{D} = -810mA$
Diode Forward Voltage (Note 4)		V_{SD}		_	-0.9	V	$V_{GS} = 0V, I_S = -0.5A$
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}		320	_	pF	V 46V V 6V
Output Capacitance		Coss	_	80	_	pF	$V_{DS} = -16V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	•	C _{rss}		60	_	pF	1 - 1.0WH12

Notes:

4. Short duration pulse test used to minimize self-heating effect.







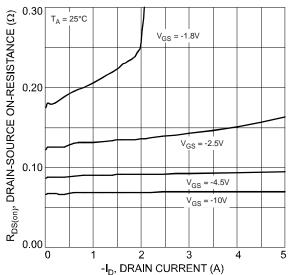


Fig. 4 On-Resistance vs Drain Current and Gate Voltage



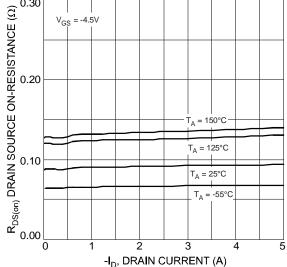


Fig. 5 Drain-Source On-Resistance Vs. Drain Current and Temperature

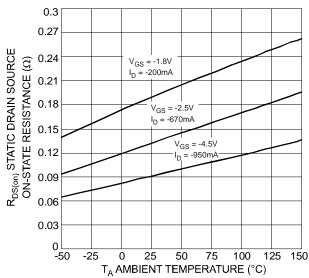


Fig. 7 Static Drain-Source On-State Resistance vs Ambient Temperature

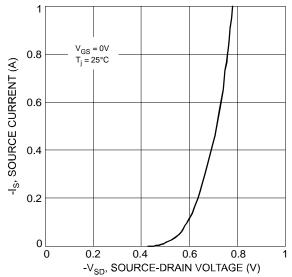
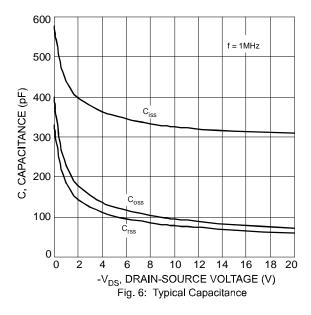
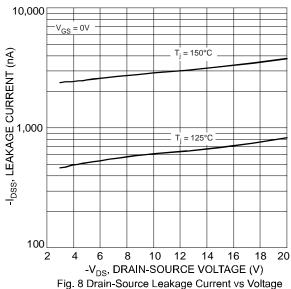


Fig. 9 Diode Forward Voltage vs. Current





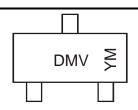


Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2240UW-7	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

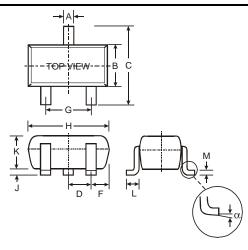


DMV = Marking Code YM = Date Code Marking Y = Year ex: V = 2008 M = Month ex: 9 = September

Date Code Key

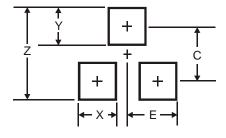
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	X		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

Package Outline Dimensions



SOT-323					
Dim	Min	Max			
Α	0.25	0.40			
В	1.15 1.35				
С	2.00	2.20			
D	0.65 N	ominal			
F	0.30	0.40			
G	1.20 1.40				
Н	1.80	2.20			
J	0.0 0.10				
K	0.90	1.00			
L	0.25	0.40			
М	0.10	0.18			
α	0°	8°			
All Di	All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Υ	0.9
С	1.9
E	1.0

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